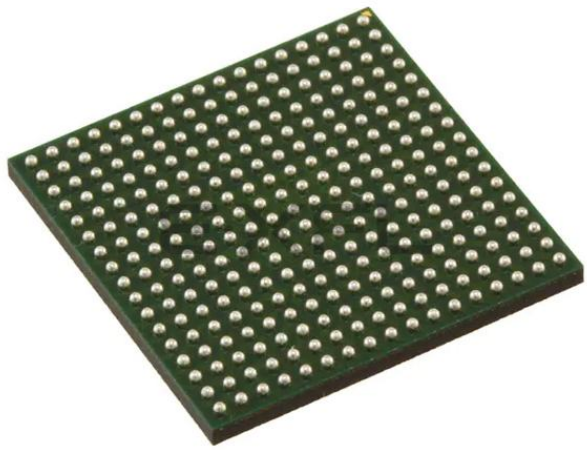


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

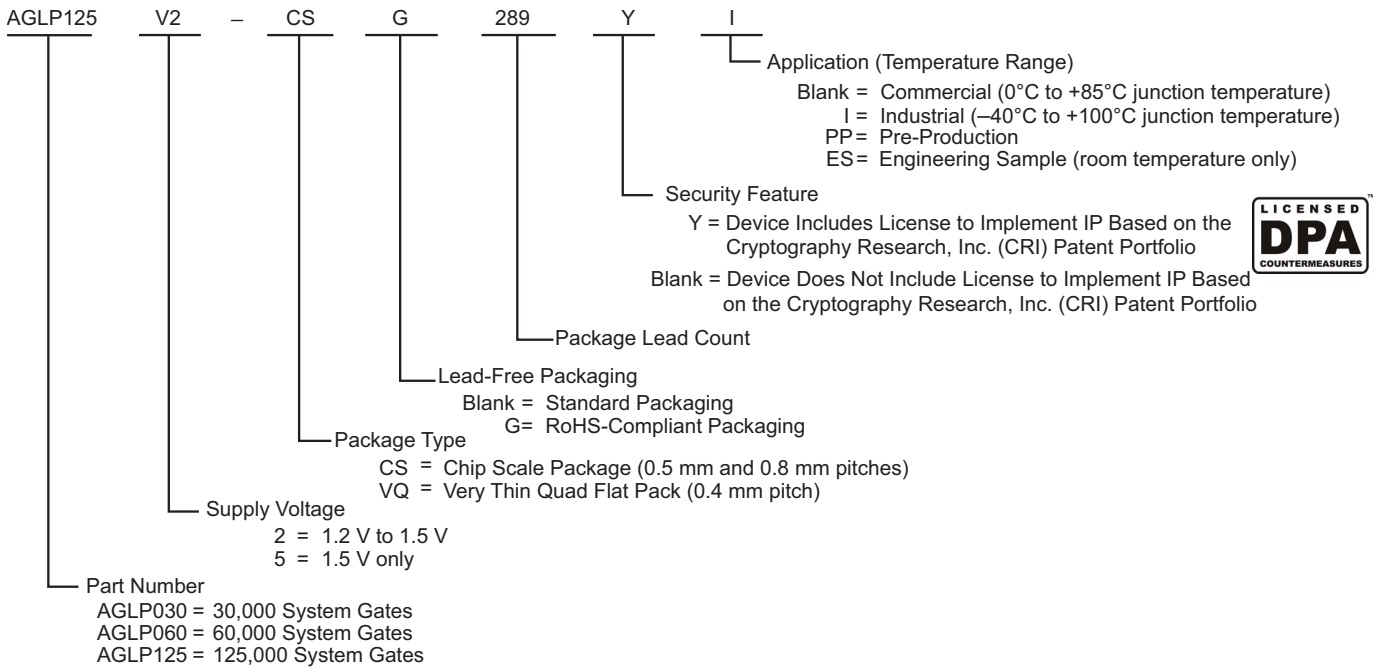
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	792
Total RAM Bits	-
Number of I/O	120
Number of Gates	30000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	289-TFBGA, CSBGA
Supplier Device Package	289-CSP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/aglp030v2-csg289i

IGLOO PLUS Ordering Information



1. *Marking information: IGLOO PLUS V2 devices do not have a V2 marking, but IGLOO PLUS V5 devices are marked accordingly.*
2. *"G" indicates RoHS-compliant packages.*

The IGLOO PLUS family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the IGLOO PLUS family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/communications, computing, and avionics markets.

Firm-Error Immunity

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of IGLOO PLUS flash-based FPGAs. Once it is programmed, the flash cell configuration element of IGLOO PLUS FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Advanced Flash Technology

The IGLOO PLUS family offers many benefits, including nonvolatility and reprogrammability, through an advanced flash-based, 130 nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

IGLOO PLUS family FPGAs utilize design and process techniques to minimize power consumption in all modes of operation.

Advanced Architecture

The proprietary IGLOO PLUS architecture provides granularity comparable to standard-cell ASICs. The IGLOO PLUS device consists of five distinct and programmable architectural features (Figure 1-1 on page 1-4):

- Flash*Freeze technology
- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory†
- Extensive CCCs and PLLs†
- Advanced I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the IGLOO PLUS core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC® family of third-generation-architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

† The AGLP030 device does not support PLL or SRAM.

VersaTiles

The IGLOO PLUS core consists of VersaTiles, which have been enhanced beyond the ProASIC[PLUS]® core tiles. The IGLOO PLUS VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to Figure 1-3 for VersaTile configurations.

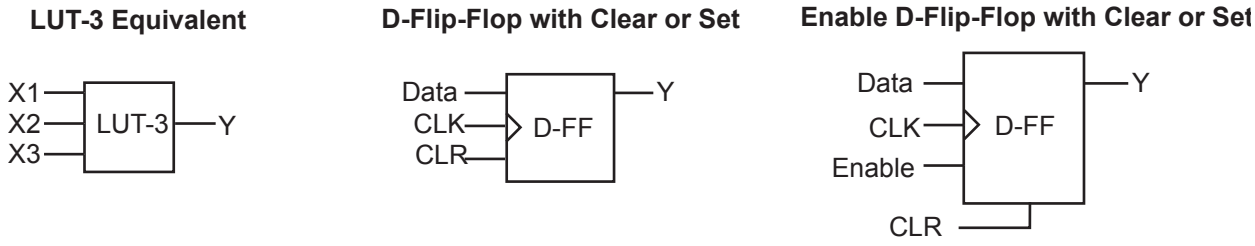


Figure 1-3 • **VersaTile Configurations**

User Nonvolatile FlashROM

IGLOO PLUS devices have 1 kbit of on-chip, user-accessible, nonvolatile FlashROM. The FlashROM can be used in diverse system applications:

- Internet protocol addressing (wireless or fixed)
- System calibration settings
- Device serialization and/or inventory control
- Subscription-based business models (for example, set-top boxes)
- Secure key storage for secure communications algorithms
- Asset management/tracking
- Date stamping
- Version management

The FlashROM is written using the standard IGLOO PLUS IEEE 1532 JTAG programming interface. The core can be individually programmed (erased and written), and on-chip AES decryption can be used selectively to securely load data over public networks (except in AGLP030 devices), as in security keys stored in the FlashROM for a user design.

The FlashROM can be programmed via the JTAG programming interface, and its contents can be read back either through the JTAG programming interface or via direct FPGA core addressing. Note that the FlashROM can only be programmed from the JTAG interface and cannot be programmed from the internal logic array.

The FlashROM is programmed as 8 banks of 128 bits; however, reading is performed on a byte-by-byte basis using a synchronous interface. A 7-bit address from the FPGA core defines which of the 8 banks and which of the 16 bytes within that bank are being read. The three most significant bits (MSBs) of the FlashROM address determine the bank, and the four least significant bits (LSBs) of the FlashROM address define the byte.

The IGLOO PLUS development software solutions, Libero® System-on-Chip (SoC) and Designer, have extensive support for the FlashROM. One such feature is auto-generation of sequential programming files for applications requiring a unique serial number in each part. Another feature allows the inclusion of static data for system version control. Data for the FlashROM can be generated quickly and easily using Libero SoC and Designer software tools. Comprehensive programming file support is also included to allow for easy programming of large numbers of parts with differing FlashROM contents.

Table 2-3 • Flash Programming Limits – Retention, Storage, and Operating Temperature [1]

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T_{STG} (°C) [2]	Maximum Operating Junction Temperature T_J (°C) [2]
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

Notes:

1. *This is a stress rating only; functional operation at any condition other than those indicated is not implied.*
2. *These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 for device operating conditions and absolute limits.*

Table 2-4 • Overshoot and Undershoot Limits [1]

VCCI	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle[2]	Maximum Overshoot/ Undershoot[2]
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. *Based on reliability requirements at 85°C.*
2. *The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.*

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every IGLOO PLUS device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-1 on page 2-4.

There are five regions to consider during power-up.

IGLOO PLUS I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points (Figure 2-1 and Figure 2-2 on page 2-5).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:
Ramping up (V5 devices): 0.6 V < trip_point_up < 1.2 V
Ramping down (V5 devices): 0.5 V < trip_point_down < 1.1 V
Ramping up (V2 devices): 0.75 V < trip_point_up < 1.05 V
Ramping down (V2 devices): 0.65 V < trip_point_down < 0.95 V

VCC Trip Point:
Ramping up (V5 devices): 0.6 V < trip_point_up < 1.1 V
Ramping down (V5 devices): 0.5 V < trip_point_down < 1.0 V

Ramping up (V2 devices): 0.65 V < trip_point_up < 1.05 V
Ramping down (V2 devices): 0.55 V < trip_point_down < 0.95 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLX exceed brownout activation levels (see Figure 2-1 and Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V ± 0.25 V for V5 devices, and 0.75 V ± 0.2 V for V2 devices), the PLL output lock signal goes Low and/or the output clock is lost. Refer to the "Brownout Voltage" section in the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *IGLOO PLUS Device Family User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

To make sure the transition from input buffers to output buffers is clean, ensure that there is no path longer than 100 ns from input buffer to output buffer in your design.

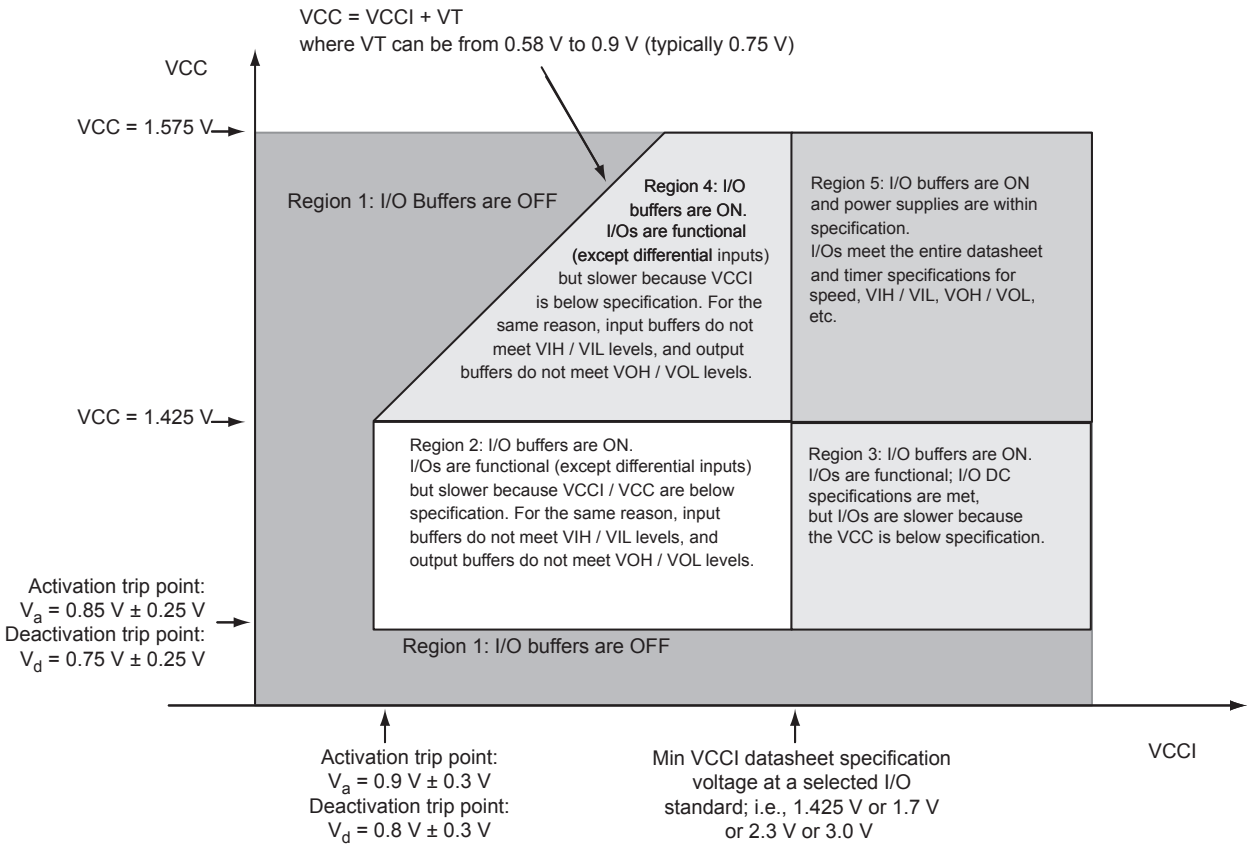


Figure 2-1 • **V5 Devices – I/O State as a Function of VCCI and VCC Voltage Levels**

– Bit 0 (LSB) = 100%
– Bit 1 = 50%
– Bit 2 = 25%
– …
– Bit 7 (MSB) = 0.78125%
– Average toggle rate = (100% + 50% + 25% + 12.5% + . . . + 0.78125%) / 8

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

***Table 2-19* • Toggle Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

***Table 2-20* • Enable Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option[2]	Slew Rate	VIL		VIH		VOL	VOH	IOL[1]	IOH[1]
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range[3]	100 µA	12 mA	High	–0.3	0.8	2	3.6	0.2	VDD 3 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	12	12
1.8 V LVCMOS	8 mA	8 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	8	8
1.5 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	4	4
1.2 V LVCMOS[4]	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS Wide Range[4,5]	100 µA	2 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	0.1	0.1

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *Note that 1.2 V LVCMOS and 3.3 V LVCMOS wide range are applicable to 100 µA drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges only.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
4. *Applicable to IGLOO PLUS V2 devices operating at $VCC_I \geq VCC$.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*

Table 2-39 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	2.92	0.19	0.99	1.37	0.67	2.97	2.38	2.25	2.70	ns
4 mA	STD	0.98	2.92	0.19	0.99	1.37	0.67	2.97	2.38	2.25	2.70	ns
6 mA	STD	0.98	2.52	0.19	0.99	1.37	0.67	2.56	2.03	2.49	3.11	ns
8 mA	STD	0.98	2.52	0.19	0.99	1.37	0.67	2.56	2.03	2.49	3.11	ns
12 mA	STD	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns
16 mA	STD	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray*

3.3 V LVCMOS Wide Range

Table 2-40 • Minimum and Maximum DC Input and Output Levels

3.3 V LVCMOS Wide Range	Equivalent Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	µA	µA	Max. µA[4]	Max. µA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	51	54	10	10
100 µA	12 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	103	109	10	10
100 µA	16 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	103	109	10	10

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < V CCI. Input current is larger when operating outside recommended ranges.*
4. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection highlighted in gray.*

Table 2-41 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	1.4	5

*Note: *Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.*

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-42 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	4 mA	STD	0.97	5.85	0.18	1.18	1.64	0.66	5.86	5.05	2.57	2.57	ns
100 µA	6 mA	STD	0.97	4.70	0.18	1.18	1.64	0.66	4.72	4.27	2.92	3.19	ns
100 µA	8 mA	STD	0.97	4.70	0.18	1.18	1.64	0.66	4.72	4.27	2.92	3.19	ns
100 µA	12 mA	STD	0.97	3.96	0.18	1.18	1.64	0.66	3.98	3.70	3.16	3.59	ns
100 µA	16 mA	STD	0.97	3.96	0.18	1.18	1.64	0.66	3.98	3.70	3.16	3.59	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-43 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	4 mA	STD	0.97	3.39	0.18	1.18	1.64	0.66	3.41	2.69	2.57	2.73	ns
100 µA	6 mA	STD	0.97	2.79	0.18	1.18	1.64	0.66	2.80	2.17	2.92	3.36	ns
100 µA	8 mA	STD	0.97	2.79	0.18	1.18	1.64	0.66	2.80	2.17	2.92	3.36	ns
100 µA	12 mA	STD	0.97	2.47	0.18	1.18	1.64	0.66	2.48	1.91	3.16	3.76	ns
100 µA	16 mA	STD	0.97	2.47	0.18	1.18	1.64	0.66	2.48	1.91	3.16	3.76	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
3. *Software default selection highlighted in gray.*

Applies to 1.2 V DC Core Voltage

Table 2-44 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	4 mA	STD	0.98	6.68	0.19	1.32	1.92	0.67	6.68	5.74	3.13	3.47	ns
100 µA	6 mA	STD	0.98	5.51	0.19	1.32	1.92	0.67	5.51	4.94	3.48	4.11	ns
100 µA	8 mA	STD	0.98	5.51	0.19	1.32	1.92	0.67	5.51	4.94	3.48	4.11	ns
100 µA	12 mA	STD	0.98	4.75	0.19	1.32	1.92	0.67	4.75	4.36	3.73	4.52	ns
100 µA	16 mA	STD	0.98	4.75	0.19	1.32	1.92	0.67	4.75	4.36	3.73	4.52	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-45 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	4 mA	STD	0.98	4.16	0.19	1.32	1.92	0.67	4.16	3.32	3.12	3.66	ns
100 µA	6 mA	STD	0.98	3.54	0.19	1.32	1.92	0.67	3.54	2.79	3.48	4.31	ns
100 µA	8 mA	STD	0.98	3.54	0.19	1.32	1.92	0.67	3.54	2.79	3.48	4.31	ns
100 µA	12 mA	STD	0.98	3.21	0.19	1.32	1.92	0.67	3.21	2.52	3.73	4.73	ns
100 µA	16 mA	STD	0.98	3.21	0.19	1.32	1.92	0.67	3.21	2.52	3.73	4.73	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
3. *Software default selection highlighted in gray.*

I/O Register Specifications

Fully Registered I/O Buffers with Asynchronous Preset

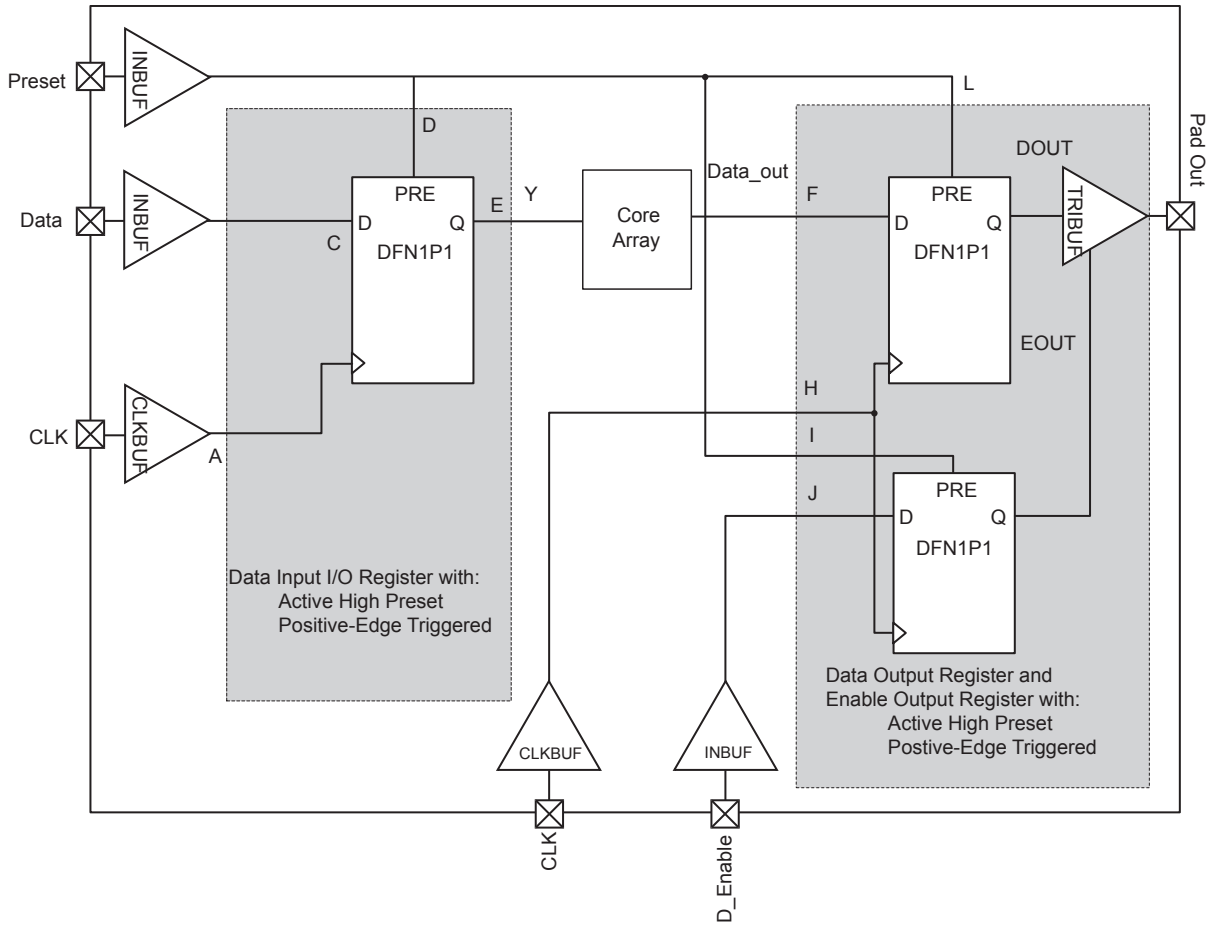


Figure 2-12 • **Timing Model of Registered I/O Buffers with Asynchronous Preset**

1.2 V DC Core Voltage

Table 2-77 • Output Data Register Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	1.03	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.52	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	1.22	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	1.31	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.24	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.24	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.19	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.19	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.31	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

1.2 V DC Core Voltage

***Table 2-94* • RAM4K9**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.28	ns
t_{AH}	Address hold time	0.25	ns
t_{ENS}	REN, WEN setup time	1.25	ns
t_{ENH}	REN, WEN hold time	0.25	ns
t_{BKS}	BLK setup time	2.54	ns
t_{BKH}	BLK hold time	0.25	ns
t_{DS}	Input data (DIN) setup time	1.10	ns
t_{DH}	Input data (DIN) hold time	0.55	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	5.51	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	4.77	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	2.82	ns
t_{C2CWWL}[1]	Address collision clk-to-clk delay for reliable write after write on same address – applicable to closing edge	0.30	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.32	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	3.21	ns
	RESET Low to data out Low on DOUT (pipelined)	3.21	ns
$t_{REMRSTB}$	RESET removal	0.93	ns
$t_{RECRSTB}$	RESET recovery	4.94	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Timing Characteristics

1.5 V DC Core Voltage

Table 2-96 • FIFO

Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.66	ns
t_{ENH}	REN, WEN Hold Time	0.13	ns
t_{BKS}	BLK Setup Time	0.30	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.63	ns
t_{DH}	Input Data (WD) Hold Time	0.20	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.77	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.50	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	2.94	ns
t_{WCKFF}	WCLK High to Full Flag Valid	2.79	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	10.71	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	2.90	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	10.60	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	1.68	ns
	RESET Low to Data Out Low on RD (pipelined)	1.68	ns
$t_{REMRSTB}$	RESET Removal	0.51	ns
$t_{RECRSTB}$	RESET Recovery	2.68	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.68	ns
t_{CYC}	Clock Cycle Time	6.24	ns
F_{MAX}	Maximum Frequency for FIFO	160	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Embedded FlashROM Characteristics

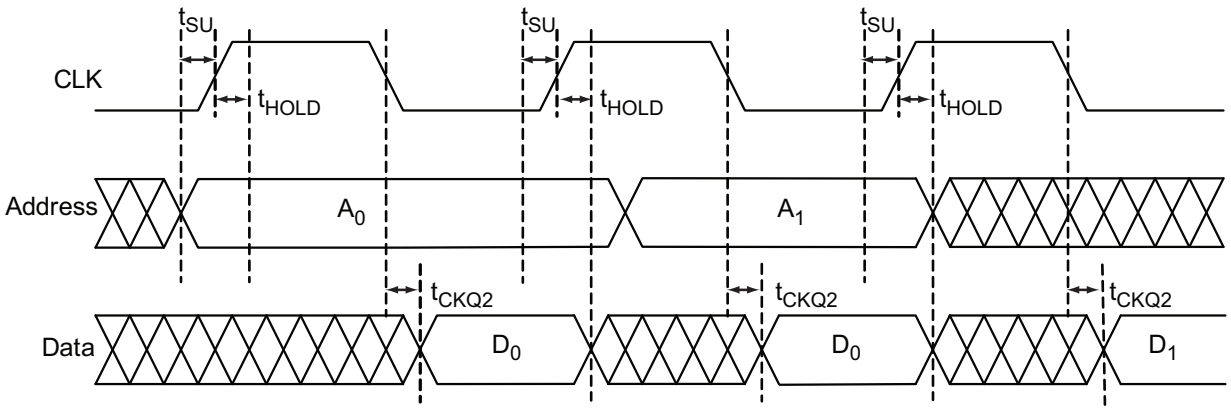


Figure 2-37 • **Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-98 • **Embedded FlashROM Access Time**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.57	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	17.58	ns
F_{MAX}	Maximum Clock Frequency	15	MHz

1.2 V DC Core Voltage

Table 2-99 • **Embedded FlashROM Access Time**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.59	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	30.94	ns
F_{MAX}	Maximum Clock Frequency	10	MHz

VCOMPLA/B/C/D/E/F PLL Ground

Ground to analog PLL power supplies. When the PLLs are not used, the Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There is one VCOMPLF pin on IGLOO PLUS devices.

VJTAG JTAG Supply Voltage

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND. It should be noted that VCC is required to be powered for JTAG operation; VJTAG alone is insufficient. If a device is in a JTAG chain of interconnected boards, the board containing the device can be powered down, provided both VJTAG and VCC to the part remain powered; otherwise, JTAG signals will not be able to transition the device, even in bypass mode.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

VPUMP Programming Supply Voltage

IGLOO PLUS devices support single-voltage ISP of the configuration flash and FlashROM. For programming, VPUMP should be 3.3 V nominal. During normal device operation, VPUMP can be left floating or can be tied (pulled up) to any voltage between 0 V and the VPUMP maximum. Programming power supply voltage (VPUMP) range is listed in the datasheet.

When the VPUMP pin is tied to ground, it will shut off the charge pump circuitry, resulting in no sources of oscillation from the charge pump circuitry.

For proper programming, 0.01 µF and 0.33 µF capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

User Pins

I/O User Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected.

During programming, I/Os become tristated and weakly pulled up to VCCI. With VCCI, VMV, and VCC supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os are instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

GL Globals

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors.

See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *IGLOO PLUS FPGA Fabric User's Guide*. All inputs labeled GC/GF are direct inputs into the quadrant clocks. For example, if GAA0 is used for an input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs labeled GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. The inputs to the global network are multiplexed, and only one input can be used as a global input.

Refer to the I/O Structure chapter of the *IGLOO PLUS FPGA Fabric User's Guide* for an explanation of the naming of global pins.

CS289	
Pin Number	AGLP030 Function
G10	GND
G11	GND
G12	IO40RSB1
G13	NC
G14	IO39RSB1
G15	IO44RSB1
G16	NC
G17	GND
H1	NC
H2	GEC0/IO108RSB3
H3	NC
H4	IO112RSB3
H5	NC
H6	IO109RSB3
H7	GND
H8	GND
H9	GND
H10	GND
H11	GND
H12	NC
H13	NC
H14	IO45RSB1
H15	VCCIB1
H16	GDB0/IO48RSB1
H17	IO42RSB1
J1	NC
J2	GEA0/IO107RSB3
J3	VCCIB3
J4	IO105RSB3
J5	NC
J6	NC
J7	VCC
J8	GND
J9	GND
J10	GND
J11	VCC
J12	IO50RSB1

CS289	
Pin Number	AGLP030 Function
J13	IO43RSB1
J14	IO51RSB1
J15	IO52RSB1
J16	GDC0/IO46RSB1
J17	GDA0/IO47RSB1
K1	GND
K2	GEB0/IO106RSB3
K3	IO102RSB3
K4	IO104RSB3
K5	IO99RSB3
K6	NC
K7	GND
K8	GND
K9	GND
K10	GND
K11	GND
K12	NC
K13	NC
K14	NC
K15	IO53RSB1
K16	GND
K17	IO49RSB1
L1	IO103RSB3
L2	IO101RSB3
L3	NC
L4	GND
L5	NC
L6	NC
L7	GND
L8	GND
L9	VCC
L10	GND
L11	GND
L12	IO58RSB1
L13	IO54RSB1
L14	VCCIB1
L15	NC

CS289	
Pin Number	AGLP030 Function
L16	NC
L17	NC
M1	NC
M2	VCCIB3
M3	IO100RSB3
M4	IO98RSB3
M5	IO93RSB3
M6	IO97RSB3
M7	NC
M8	NC
M9	IO71RSB2
M10	NC
M11	IO63RSB2
M12	NC
M13	IO57RSB1
M14	NC
M15	NC
M16	NC
M17	VCCIB1
N1	NC
N2	NC
N3	IO95RSB3
N4	IO96RSB3
N5	GND
N6	NC
N7	IO85RSB2
N8	IO79RSB2
N9	IO77RSB2
N10	VCCIB2
N11	NC
N12	NC
N13	IO59RSB2
N14	NC
N15	GND
N16	IO56RSB1
N17	IO55RSB1
P1	IO94RSB3

CS289	
Pin Number	AGLP030 Function
P2	NC
P3	GND
P4	NC
P5	NC
P6	IO87RSB2
P7	IO80RSB2
P8	GND
P9	IO72RSB2
P10	IO67RSB2
P11	IO61RSB2
P12	NC
P13	VCCIB2
P14	NC
P15	IO60RSB2
P16	IO62RSB2
P17	VJTAG
R1	GND
R2	IO91RSB2
R3	NC
R4	NC
R5	NC
R6	VCCIB2
R7	IO83RSB2
R8	IO78RSB2
R9	IO74RSB2
R10	IO70RSB2
R11	GND
R12	NC
R13	NC
R14	NC
R15	NC
R16	TMS
R17	TRST
T1	IO92RSB3
T2	IO89RSB2
T3	NC
T4	GND

CS289	
Pin Number	AGLP030 Function
T5	NC
T6	IO84RSB2
T7	IO81RSB2
T8	IO76RSB2
T9	VCCIB2
T10	IO69RSB2
T11	IO65RSB2
T12	IO64RSB2
T13	NC
T14	GND
T15	NC
T16	TDI
T17	TDO
U1	FF/IO90RSB2
U2	GND
U3	NC
U4	IO88RSB2
U5	IO86RSB2
U6	IO82RSB2
U7	GND
U8	IO75RSB2
U9	IO73RSB2
U10	IO68RSB2
U11	IO66RSB2
U12	GND
U13	NC
U14	NC
U15	NC
U16	TCK
U17	VPUMP

Revision	Changes	Page
Revision 12 (continued)	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—P_{CLOCK}" section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the *IGLOO PLUS FPGA Fabric User's Guide* (SAR 34733).	2-12
	t_{DOUT} was corrected to t_{DIN} in Figure 2-4 • Input Buffer Timing Model and Delays (example) (SAR 37107).	2-16
	The AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34887).	2-27
	Minimum pulse width High and Low values were added to the tables in the "Global Tree Timing Characteristics" section. The maximum frequency for global clock parameter was removed from these tables because a frequency on the global is only an indication of what the global network can do. There are other limiters such as the SRAM, I/Os, and PLL. SmartTime software should be used to determine the design frequency (SAR 36963).	2-58
	Table 2-90 • IGLOO PLUS CCC/PLL Specification and Table 2-91 • IGLOO PLUS CCC/PLL Specification were updated. A note was added to both tables indicating that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 34820). The value for serial clock was missing from these tables and has been restored. The value and units for input cycle-to-cycle jitter were incorrect and have been restored. The note to Table 2-90 • IGLOO PLUS CCC/PLL Specification giving specifications for which measurements done was corrected from VCC/VCCPLL = 1.14 V to VCC/VCCPLL = 1.425 V. The Delay Range in Block: Programmable Delay 2 value in Table 2-91 • IGLOO PLUS CCC/PLL Specification was corrected from 0.025 to 0.863 (SAR 37058).	2-61, 2-62
	Figure 2-28 • Write Access after Read onto Same Address was deleted. Reference was made to a new application note, *Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*, which covers these cases in detail (SAR 34868). The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-32 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SAR 35748).	2-65, 2-68, 2-74, 2-76
	The "Pin Descriptions and Packaging" chapter has been added (SAR 34769).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in *Package Mechanical Drawings* (SAR 34769).	4-1
Revision 11 (July 2010)	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "IGLOO PLUS Device Status" table indicates the status for each device in the family.	N/A
	The "Reprogrammable Flash Technology" section was revised to add "250 MHz (1.5 V systems) and 160 MHz (1.2 V systems) System Performance."	I
	The "I/Os with Advanced I/O Standards" section was revised to add definitions for hot-swap and cold-sparing.	1-6
	Conditional statements regarding hot insertion were removed from the description of VI in Table 2-1 • Absolute Maximum Ratings, since all IGLOO PLUS devices are hot insertion enabled.	2-1

Revision	Changes	Page
Revision 11 (continued)	The tables in the "Single-Ended I/O Characteristics" section were updated. Notes clarifying IIL and IIH were added. Tables for 3.3 V LVCMOS and 1.2 V LVCMOS wide range were added (SAR 79370, SAR 79353, and SAR 79366). Notes in the wide range tables state that the minimum drive strength for any LVCMOS 3.3 V (or LVCMOS 1.2 V) software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 25700).	2-27
	The following sentence was deleted from the "2.5 V LVCMOS" section: It uses a 5 V–tolerant input buffer and push-pull output buffer (SAR 24916).	2-32
	The tables in the "Input Register" section, "Output Register" section, and "Output Enable Register" section were updated. The tables in the "VersaTile Characteristics" section were updated.	2-45 through 2-56
	The following tables were updated in the "Global Tree Timing Characteristics" section: Table 2-85 • AGLP060 Global Resource (1.5 V) Table 2-86 • AGLP125 Global Resource (1.5 V) Table 2-88 • AGLP060 Global Resource (1.2 V)	2-58
	Table 2-90 • IGLOO PLUS CCC/PLL Specification and Table 2-91 • IGLOO PLUS CCC/PLL Specification were revised (SAR 79388). VCO output jitter and maximum peak-to-peak jitter data were changed. Three notes were added to the table in connection with these changes.	2-61
	Figure 2-28 • Write Access after Write onto Same Address and Figure 2-29 • Write Access after Read onto Same Address were deleted.	N/A
	The tables in the "SRAM", "FIFO" and "Embedded FlashROM Characteristics" sections were updated.	2-68, 2-78